

BT138 series D and E

12 A four-quadrant triacs, sensitive gate
Rev. 02 — 12 March 2008

Product data sheet

Product profile

1.1 General description

Passivated sensitive gate triac in a SOT78 plastic package.

1.2 Features

- Very sensitive gate
- Direct interfacing to logic level ICs
- Gate triggering in four quadrants
- Direct interfacing to low power gate drive circuits

1.3 Applications

- General purpose switching and phase control
- 230 V lamp dimmers

1.4 Quick reference data

- $V_{DRM} \le 600 \text{ V (BT138-600D)}$
- V_{DRM} ≤ 600 V (BT138-600E)
- V_{DRM} ≤ 800 V (BT138-800E)
- $I_{GT} \le 5 \text{ mA (BT138-600D)}$
- $I_{GT} \le 10 \text{ mA (BT138-600E)}$
- $I_{GT} \le 10 \text{ mA (BT138-800E)}$
- $I_{T(RMS)} \le 12 A$
- $I_{TSM} \le 95 \text{ A (t = 20 ms)}$
- $I_{GT} \le 10 \text{ mA } (T2-G+) \text{ (BT138-600D)}$
- $I_{GT} \le 25 \text{ mA } (T2-G+) \text{ (BT138-600E)}$
- $I_{GT} \le 25 \text{ mA } (T2-G+) (BT138-800E)$



2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	main terminal 1 (T1)		N.I.
2	main terminal 2 (T2)	mb	T2—T1
3	gate (G)		sym051
mb	mounting base; main terminal 2 (T2)	1 2 3	
		SOT78 (TO-220AB)	

3. Ordering information

Table 2. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BT138-600D	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead	SOT78			
BT138-600E		TO-220AB				
BT138-800E						

4. Limiting values

Table 3. Limiting values

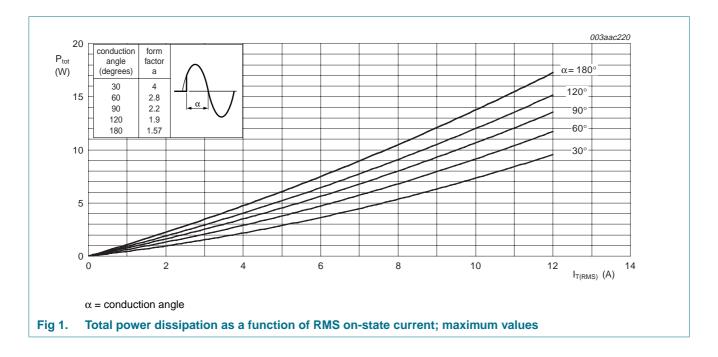
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage				
		BT138-600D	<u>[1]</u> _	600	V
		BT138-600E	<u>[1]</u> _	600	V
		BT138-800E	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 99 ^{\circ}\text{C}$; see Figure 4 and 5	-	12	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3			
		t = 20 ms	-	95	Α
		t = 16.7 ms	-	105	Α
l ² t	I ² t for fusing	t _p = 10 ms	-	45	A ² s

Table 3. Limiting values ...continued
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
dl _T /dt rate of rise of on-sta	rate of rise of on-state current	$I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$			
		T2+ G+	-	50	A/μs
		T2+ G-	-	50	A/μs
		T2- G-	-	50	A/μs
		T2- G+	-	10	A/μs
I _{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	125	°C

^[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/μ s.



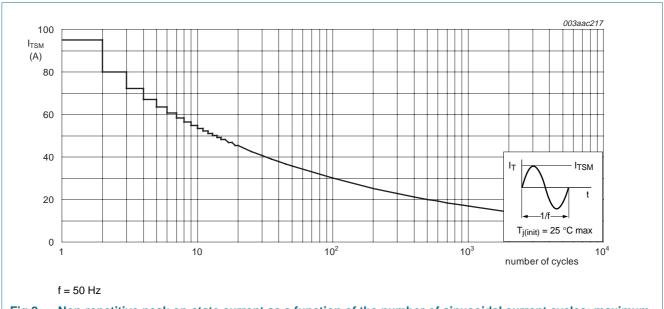
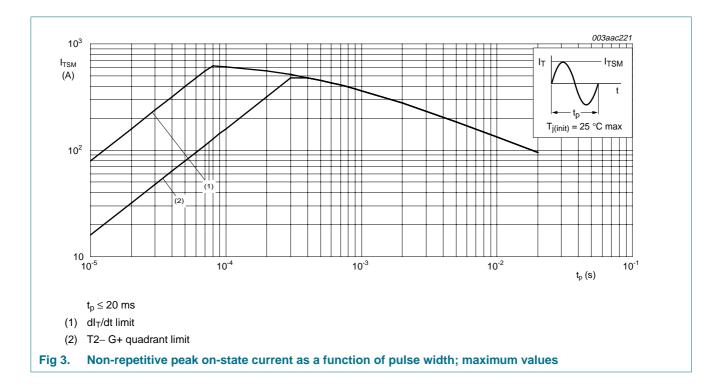


Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



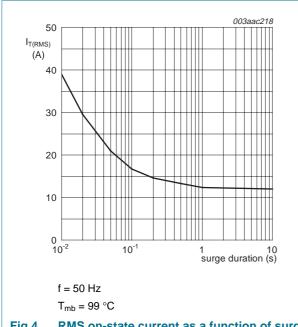


Fig 4. RMS on-state current as a function of surge duration; maximum values

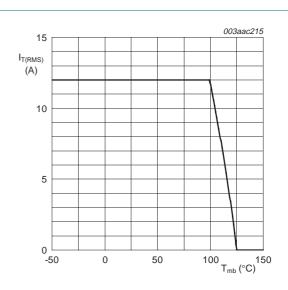
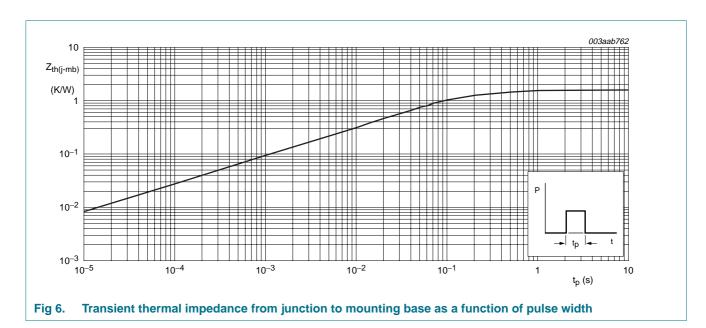


Fig 5. RMS on-state current as a function of mounting base temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; see Figure 6	-	-	1.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	full cycle; in free air	-	60	-	K/W



6. Static characteristics

Table 5. Static characteristics

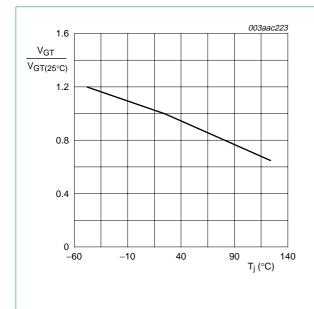
 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

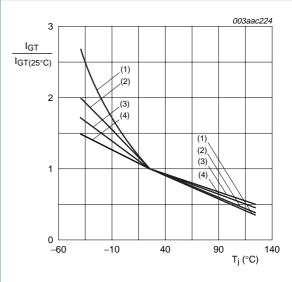
Symbol	Parameter	Conditions	BT138	BT138-600D			BT138-600E BT138-800E		
			Min	Тур	Max	Min	Тур	Max	
I _{GT} gate trigger current		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A};$ see Figure 8	'		'		'	'	'
		T2+ G+	-	1.3	5	-	2.5	10	mΑ
		T2+ G-	-	2.8	5	-	4.0	10	mΑ
		T2- G-	-	3.2	5	-	5.0	10	mΑ
		T2- G+	-	5.5	10	-	11	25	mΑ
I _L latching current		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A};$ see Figure 10							
		T2+ G+	-	-	15	-	-	30	mA
		T2+ G-	-	-	20	-	-	40	mΑ
		T2- G-	-	-	15	-	-	30	mA
		T2- G+	-	-	20	-	-	40	mA
I _H	holding current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A};$ see Figure 11	-	-	10	-	-	30	mA
V_{T}	on-state voltage	I _T = 15 A; see Figure 9	-	1.4	1.65	-	1.4	1.65	V
V_{GT}	gate trigger voltage	$I_T = 0.1 \text{ A}$; see Figure 7							
		V _D = 12 V;	-	0.7	1.5	-	0.7	1.5	V
		$V_D = V_{DRM}$; $T_j = 125 ^{\circ}C$	0.25	0.4	-	0.25	0.4	-	V
I _D	off-state current	$V_D = V_{DRM(max)};$ $T_j = 125 ^{\circ}C$	-	0.1	0.5	-	0.1	0.5	mA

7. Dynamic characteristics

Table 6. Dynamic characteristics

Symbol Parameter		Conditions	BT138-600D			BT138	Unit		
			Min	Тур	Max	Min	Тур	Max	
dV _D /dt	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)};$ exponential waveform; gate open circuit; $T_j = 110 ^{\circ}C$	-	50	-	-	150	-	V/μs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 16 \text{ A};$ $V_D = V_{DRM(max)};$ $I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A/}\mu\text{s}$	-	2	-	-	2	-	μs

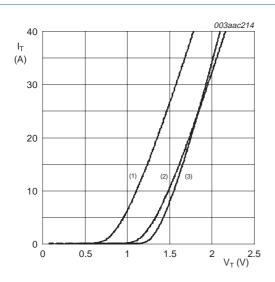




- (1) T2-G+
- (2) T2-G-
- (3) T2+ G-
- (4) T2+ G+

Fig 7. Normalized gate trigger voltage as a function of junction temperature

Fig 8. Normalized gate trigger current as a function of junction temperature



 $V_0 = 1.175 \text{ V}$

 $R_s = 0.032 \Omega$

(1) $T_i = 125$ °C; typical values

(2) $T_i = 125 \,^{\circ}C$; maximum values

(3) $T_j = 25$ °C; maximum values

Fig 9. On-state current as a function of on-state voltage

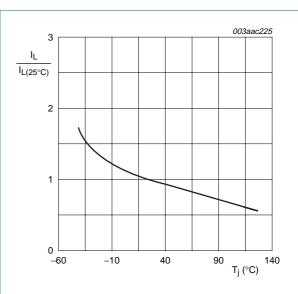


Fig 10. Normalized latching current as a function of junction temperature

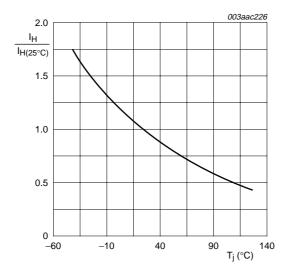


Fig 11. Normalized holding current as a function of junction temperature

8. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

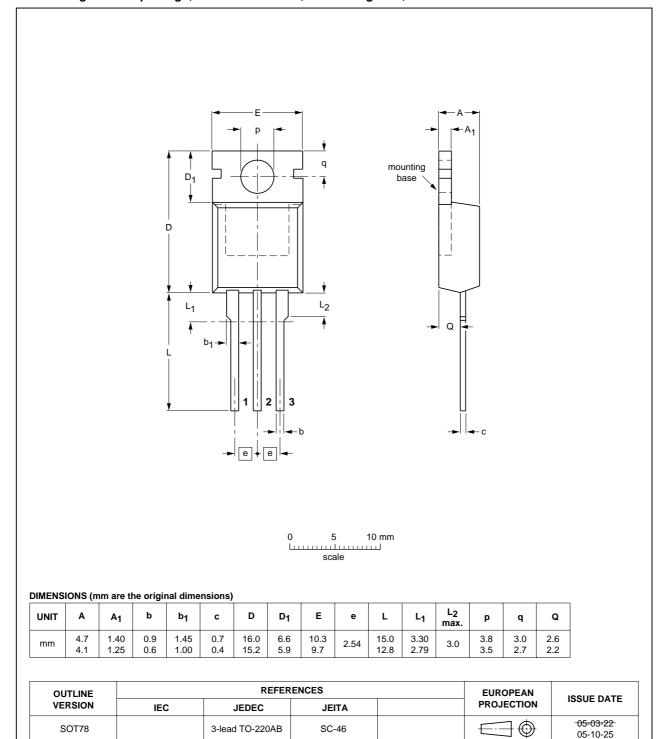


Fig 12. Package outline SOT78 (TO-220AB)

9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BT138_SER_D_E_2	20080312	Product data sheet	-	BT138_SERIES_E_1		
Modifications:		The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.				
	 Legal texts 	have been adapted to the n	ew company name whe	re appropriate.		
	 BT138-600I 	O product added				
BT138_SERIES_E_1	19970901	Product data sheet	-	-		

BT138 series D and E

12 A four-quadrant triacs, sensitive gate

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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